

March 2007

# **FJP13009**

# **High Voltage Fast-Switching NPN Power Transistor**

- High Voltage Capability
- · High Switching Speed
- · Suitable for Electronic Ballast and Switching Mode Power Supply



1.Base 2.Collector 3.Emitter

### Absolute Maximum Ratings\* T<sub>C</sub> = 25°C unless otherwise noted (notes\_1)

Symbol	Parameter 4	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	700	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	9	V
I <sub>C</sub>	Collector Current (DC)	12	A
I <sub>CP</sub>	Collector Current (Pulse)	24	А
I <sub>B</sub>	Base Current	6	A
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> = 25°C)	100	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature Range	-65 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES\_1:

### **Package Marking and Ordering Information**

Device Item (notes_2)	Device Marking	Package	Packing Method	Qty(pcs)
FJP13009	J13009	TO-220	Bulk	1,200
FJP13009H2TU	J130092	TO-220	TUBE	1,000
FJP13009TU	J13009	TO-220	TUBE	1,000

<sup>1)</sup> These ratings are based on a maximum junction temperature of 150°C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

<sup>1)</sup> The Affix "-H2" means the hFE classification.

<sup>2)</sup> The Suffix "-TU" means the Tube packing method, which can be on fairchildsemi website at http://www.fairchildsemi.com/packaging.

## **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage	$I_C = 10 \text{mA}, I_B = 0$	400			V
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$			1	mA
h <sub>FE</sub>	* DC Current Gain	$V_{CE} = 5V, I_{C} = 5A (h_{FE1})$ $V_{CE} = 5V, I_{C} = 8A$	8 6		40 30	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_C = 5A$ , $I_B = 1A$ $I_C = 8A$ , $I_B = 1.6A$ $I_C = 12A$ , $I_B = 3A$			1 1.5 3	V V V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	$I_C = 5A, I_B = 1A$ $I_C = 8A, I_B = 1.6A$			1.2 1.6	V V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, f = 0.1MHz		180		pF
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.5A$	4			MHz
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> = 125V, I <sub>C</sub> = 8A			1.1	μS
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = 1.6A, R_L = 15,6\Omega$			3	μS
t <sub>F</sub>	Fall Time				0.7	μS

<sup>\*</sup> Pulse Test: PW  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%

# h<sub>FE</sub> Classification

ssification		4
Classification	H1	H2
h <sub>FE1</sub>	8 ~ 17	15 ~ 28
		.com.

### **Typical Performance Characteristics**

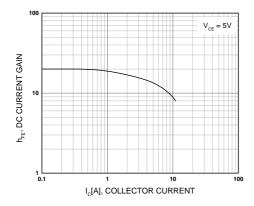


Figure 1. DC current Gain

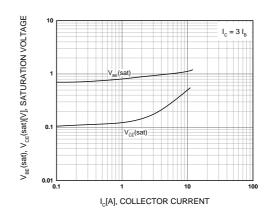


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

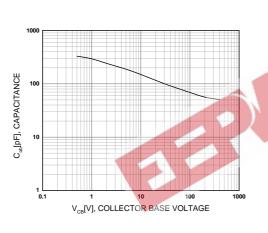


Figure 3. Collector Output Capacitance

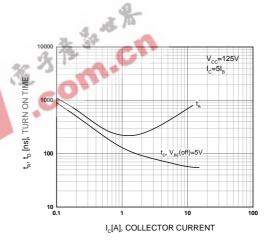


Figure 4. Turn On Time

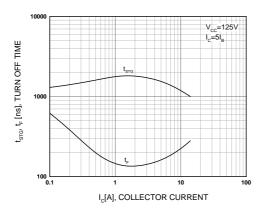


Figure 5. Turn Off Time

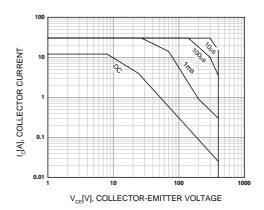
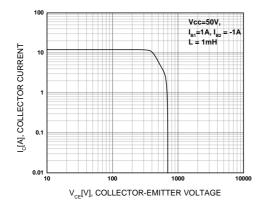


Figure 6. Forward Bias Safe Operating Area

### Typical Performance Characteristics (Continued)





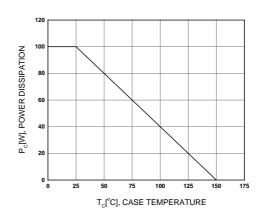


Figure 8. Power Derating



### **Mechanical Dimensions** TO-220 4.50 ±0.20 9.90 ±0.20 (8.70) $.30 \pm 0.10$ $2.80 \pm 0.10$ (1.70) 1.30 +0.10 -0.05 ø3.60 ±0.10 (3.70) 18.95MAX 15.90 ±0.20 9.20 ±0.20 (1.46)(3.00)(1.00)13.08 ±0.20 1.27 ±0.10 0.80 ±0.10 0.50 +0.10 -0.05 2.40 ±0.20 2.54TYP 2.54TYP [2.54 ±0.20] [2.54 ±0.20]

10.00 ±0.20

Dimensions in Millimeters





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